

BCR8CS

Refer to the page 6 as to the product guaranteed maximum junction temperature 150°C

MEDIUM POWER USE
NON-INSULATED TYPE, PLANAR PASSIVATION TYPE

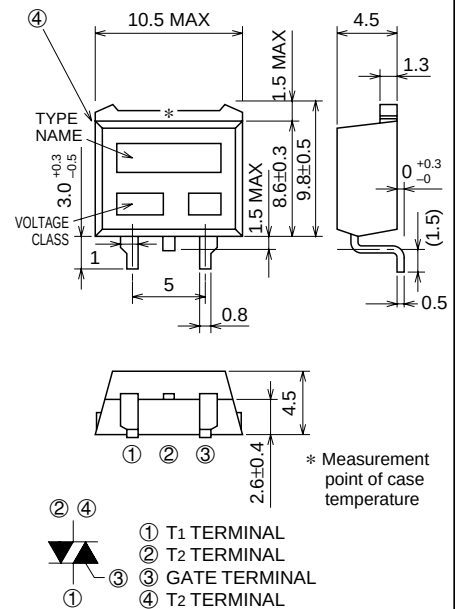
BCR8CS



- IT (RMS) 8A
- VDRM 600V
- I_{FGT I}, I_{RGT I}, I_{RGT III} 20mA

OUTLINE DRAWING

Dimensions
in mm



TO-220S

APPLICATION

Solid state relay, hybrid IC

MAXIMUM RATINGS

Symbol	Parameter	Voltage class	Unit
		12	
V _{DRM}	Repetitive peak off-state voltage *1	600	V
V _{DSM}	Non-repetitive peak off-state voltage *1	720	V

Symbol	Parameter	Conditions	Ratings	Unit
IT (RMS)	RMS on-state current	Commercial frequency, sine full wave 360° conduction, Tc=105°C*3	8	A
ITSM	Surge on-state current	60Hz sinewave 1 full cycle, peak value, non-repetitive	80	A
I ² t	I ² t for fusing	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current	26	A ² s
PGM	Peak gate power dissipation		5	W
PG (AV)	Average gate power dissipation		0.5	W
VGM	Peak gate voltage		10	V
IGM	Peak gate current		2	A
Tj	Junction temperature		−40 ~ +125	°C
Tstg	Storage temperature		−40 ~ +125	°C
—	Weight	Typical value	1.2	g

*1. Gate open.

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Refer to the page 6 as to the product guaranteed
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MEDIUM POWER USE
NON-INSULATED TYPE, PLANAR PASSIVATION TYPE

ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
I_{DRM}	Repetitive peak off-state current	$T_J=125^{\circ}\text{C}$, V_{DRM} applied	—	—	2.0	mA
V_{TM}	On-state voltage	$T_c=25^{\circ}\text{C}$, $I_{TM}=12\text{A}$, Instantaneous measurement	—	—	1.5	V
$V_{FGT\text{ I}}$	Gate trigger voltage *2	$T_J=25^{\circ}\text{C}$, $V_D=6\text{V}$, $R_L=6\Omega$, $R_G=330\Omega$	—	—	1.5	V
$V_{RGT\text{ I}}$			—	—	1.5	V
$V_{RGT\text{ III}}$			—	—	1.5	V
$I_{FGT\text{ I}}$	Gate trigger current *2	$T_J=25^{\circ}\text{C}$, $V_D=6\text{V}$, $R_L=6\Omega$, $R_G=330\Omega$	—	—	20	mA
$I_{RGT\text{ I}}$			—	—	20	mA
$I_{RGT\text{ III}}$			—	—	20	mA
V_{GD}	Gate non-trigger voltage	$T_J=125^{\circ}\text{C}$, $V_D=1/2V_{DRM}$	0.2	—	—	V
$R_{th(j-c)}$	Thermal resistance	Junction to case *3 *4	—	—	2.0	$^{\circ}\text{C}/\text{W}$
$(dv/dt)_c$	Critical-rate of rise of off-state commutating voltage *5	$T_J=125^{\circ}\text{C}$	10	—	—	$\text{V}/\mu\text{s}$

*2. Measurement using the gate trigger characteristics measurement circuit.

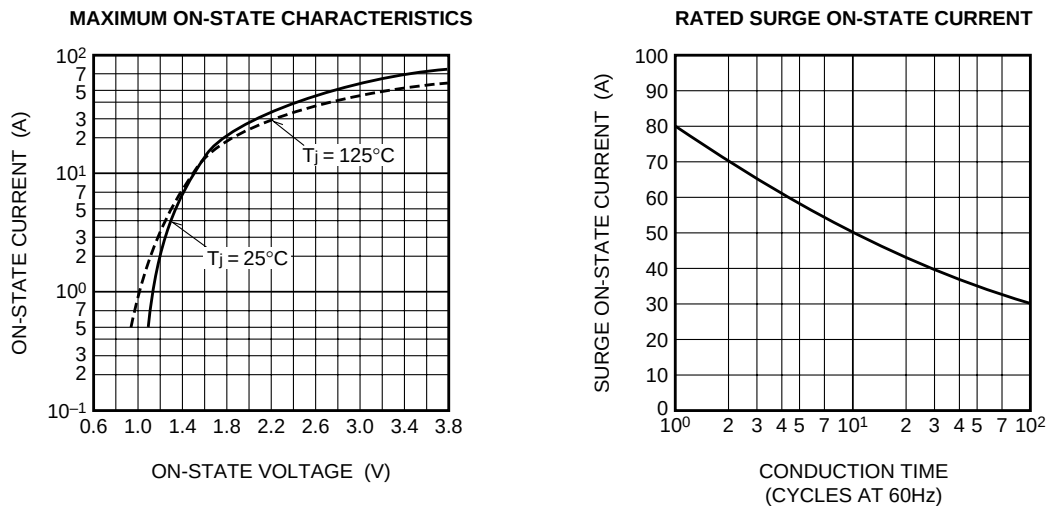
*3. Case temperature is measured on the T2 terminal.

*4. The contact thermal resistance $R_{th(c-j)}$ in case of greasing is $1.0^{\circ}\text{C}/\text{W}$.

*5. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.

Test conditions	Commutating voltage and current waveforms (inductive load)
1. Junction temperature $T_J=125^{\circ}\text{C}$ 2. Rate of decay of on-state commutating current $(di/dt)_c=-4.0\text{A}/\text{ms}$ 3. Peak off-state voltage $V_D=400\text{V}$	

PERFORMANCE CURVES

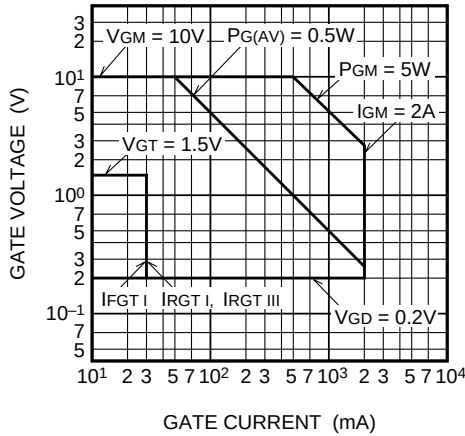


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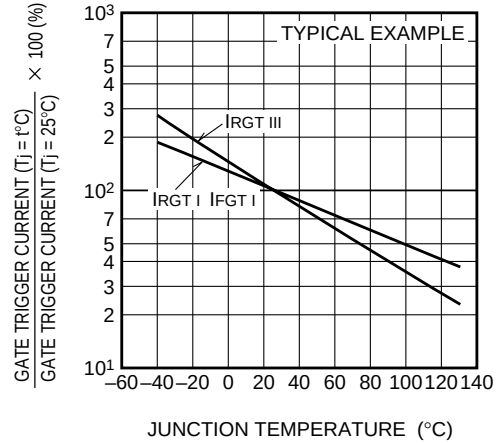
Refer to the page 6 as to the product guaranteed maximum junction temperature 150°C

MEDIUM POWER USE
NON-INSULATED TYPE, PLANAR PASSIVATION TYPE

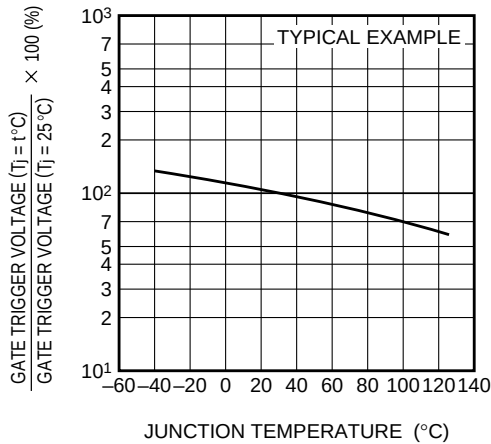
**GATE CHARACTERISTICS
(I, II AND III)**



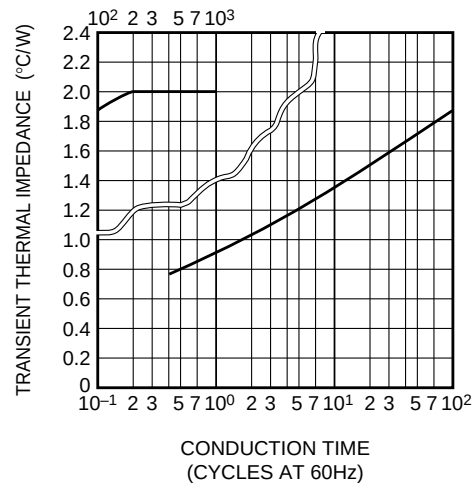
**GATE TRIGGER CURRENT VS.
JUNCTION TEMPERATURE**



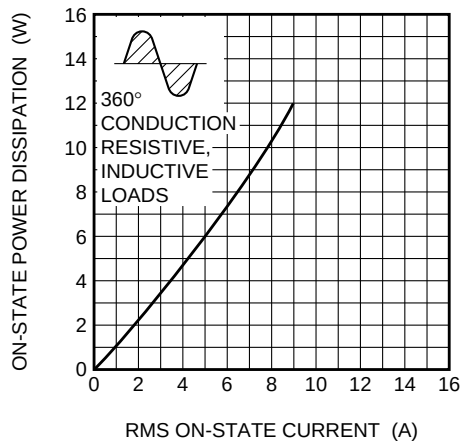
**GATE TRIGGER VOLTAGE VS.
JUNCTION TEMPERATURE**



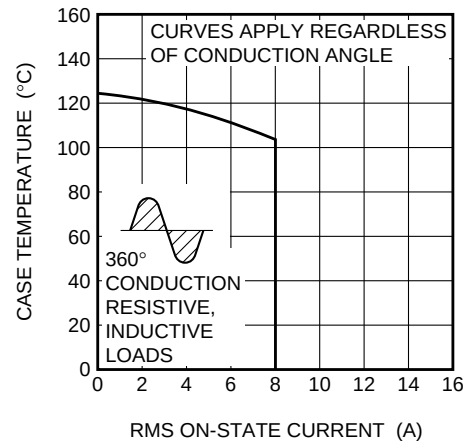
**MAXIMUM TRANSIENT THERMAL
IMPEDANCE CHARACTERISTICS
(JUNCTION TO CASE)**



**MAXIMUM ON-STATE POWER
DISSIPATION**



**ALLOWABLE CASE TEMPERATURE
VS. RMS ON-STATE CURRENT**

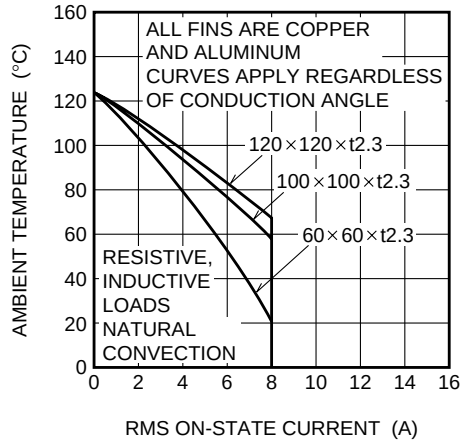


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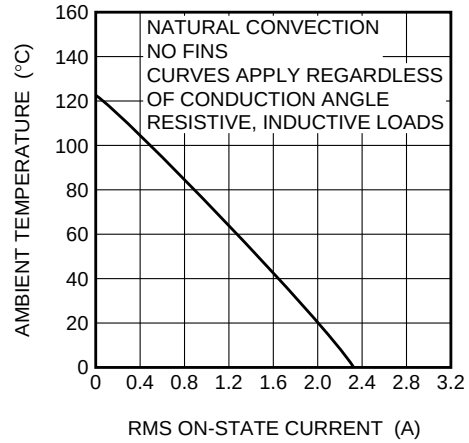
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MEDIUM POWER USE
NON-INSULATED TYPE, PLANAR PASSIVATION TYPE

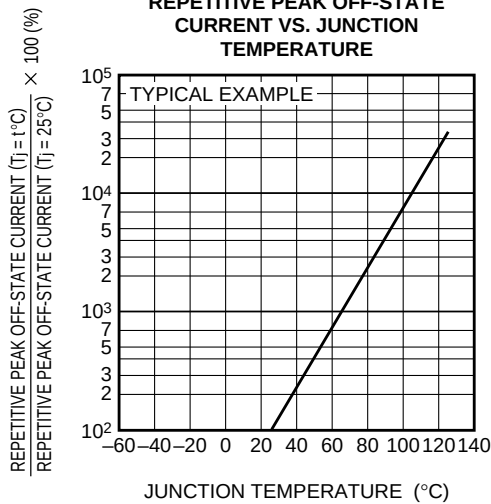
ALLOWABLE AMBIENT TEMPERATURE
VS. RMS ON-STATE CURRENT



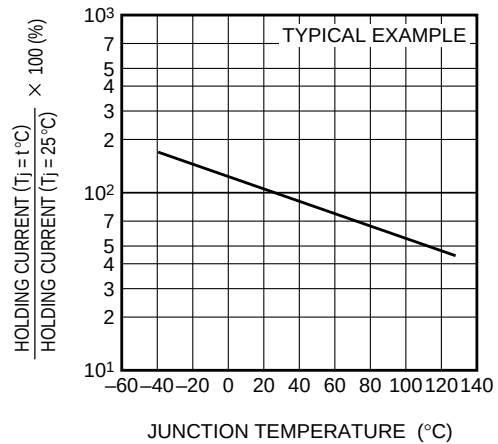
ALLOWABLE AMBIENT TEMPERATURE
VS. RMS ON-STATE CURRENT



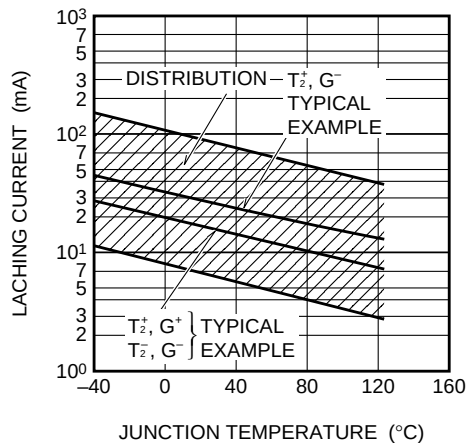
REPETITIVE PEAK OFF-STATE
CURRENT VS. JUNCTION
TEMPERATURE



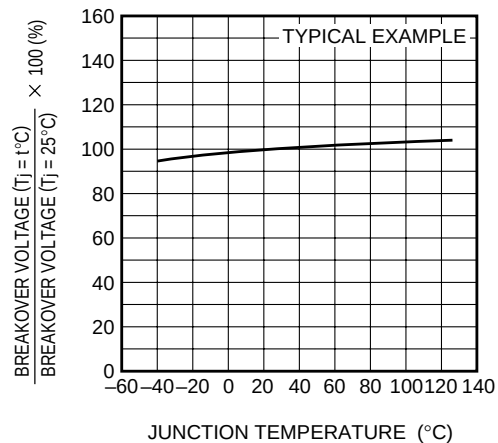
HOLDING CURRENT VS.
JUNCTION TEMPERATURE



LATCHING CURRENT VS.
JUNCTION TEMPERATURE



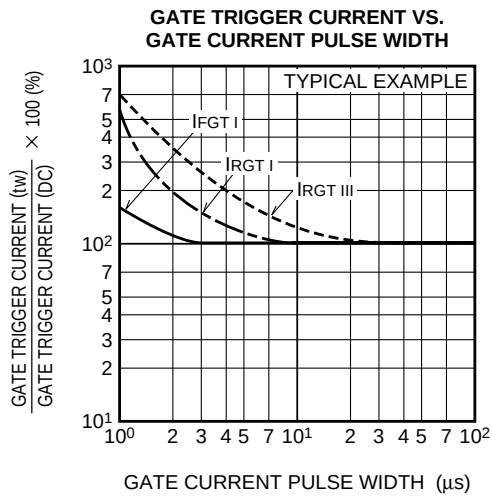
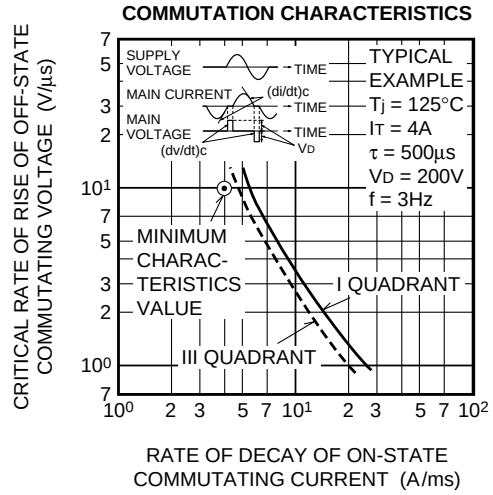
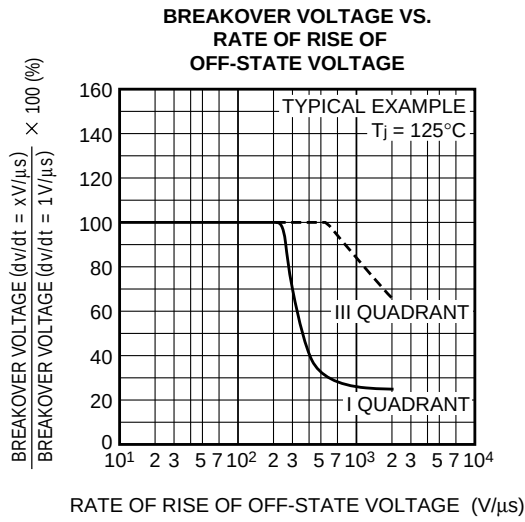
BREAKOVER VOLTAGE VS.
JUNCTION TEMPERATURE



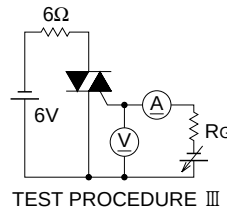
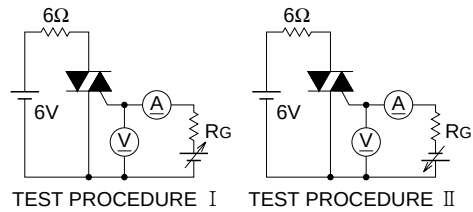
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MEDIUM POWER USE
NON-INSULATED TYPE, PLANAR PASSIVATION TYPE



GATE TRIGGER CHARACTERISTICS TEST CIRCUITS



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The product guaranteed maximum junction temperature 150°C (See warning.)

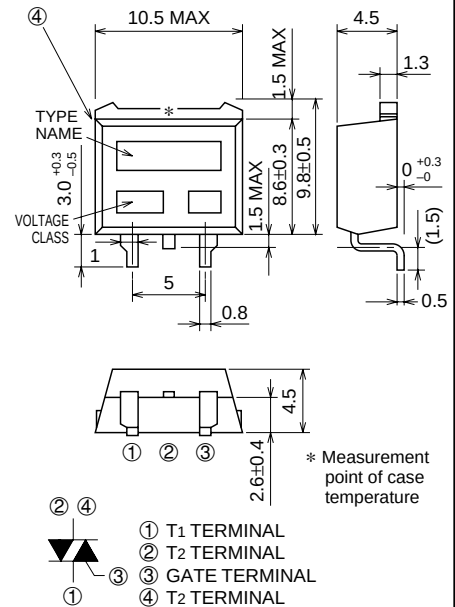
MEDIUM POWER USE
NON-INSULATED TYPE, PLANAR PASSIVATION TYPE

BCR8CS

- **IT (RMS)** **8A**
- **VDRM** **600V**
- **IFGT I , IRGT I , IRGT III** **20mA**

OUTLINE DRAWING

Dimensions
in mm



TO-220S

APPLICATION

Solid state relay, hybrid IC

(Warning)

1. Refer to the recommended circuit values around the triac before using.
2. Be sure to exchange the specification before using. If not exchanged, general triacs will be supplied.

MAXIMUM RATINGS

Symbol	Parameter	Voltage class	Unit
		12	
VDRM	Repetitive peak off-state voltage *1	600	V
VDSM	Non-repetitive peak off-state voltage *1	720	V

Symbol	Parameter	Conditions	Ratings	Unit
IT (RMS)	RMS on-state current	Commercial frequency, sine full wave 360° conduction, T _c =130°C*3	8	A
ITSM	Surge on-state current	60Hz sinewave 1 full cycle, peak value, non-repetitive	80	A
I ² _t	I ² _t for fusing	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current	26	A ² s
PGM	Peak gate power dissipation		5	W
PG (AV)	Average gate power dissipation		0.5	W
VGM	Peak gate voltage		10	V
IGM	Peak gate current		2	A
T _j	Junction temperature		-40 ~ +150	°C
T _{stg}	Storage temperature		-40 ~ +150	°C
—	Weight	Typical value	1.2	g

*1. Gate open.

Mar. 2002

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NON-INSULATED TYPE, PLANAR PASSIVATION TYPE

ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
I_{DRM}	Repetitive peak off-state current	$T_J=150^{\circ}\text{C}$, V_{DRM} applied	—	—	2.0	mA
V_{TM}	On-state voltage	$T_c=25^{\circ}\text{C}$, $I_{TM}=12\text{A}$, Instantaneous measurement	—	—	1.5	V
$V_{FGT\text{ I}}$	Gate trigger voltage *2	$T_J=25^{\circ}\text{C}$, $V_D=6\text{V}$, $R_L=6\Omega$, $R_G=330\Omega$	—	—	1.5	V
$V_{RGT\text{ I}}$			—	—	1.5	V
$V_{RGT\text{ III}}$			—	—	1.5	V
$I_{FGT\text{ I}}$	Gate trigger current *2	$T_J=25^{\circ}\text{C}$, $V_D=6\text{V}$, $R_L=6\Omega$, $R_G=330\Omega$	—	—	20	mA
$I_{RGT\text{ I}}$			—	—	20	mA
$I_{RGT\text{ III}}$			—	—	20	mA
V_{GD}	Gate non-trigger voltage	$T_J=125^{\circ}\text{C}/150^{\circ}\text{C}$, $V_D=1/2V_{DRM}$	0.2/0.1	—	—	V
$R_{th(j-c)}$	Thermal resistance	Junction to case *3 *4	—	—	2.0	$^{\circ}\text{C}/\text{W}$
$(dv/dt)_c$	Critical-rate of rise of off-state commutating voltage *5	$T_J=125^{\circ}\text{C}/150^{\circ}\text{C}$	10/1	—	—	$\text{V}/\mu\text{s}$

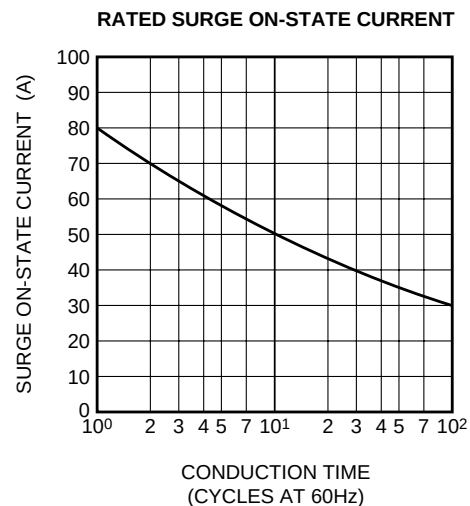
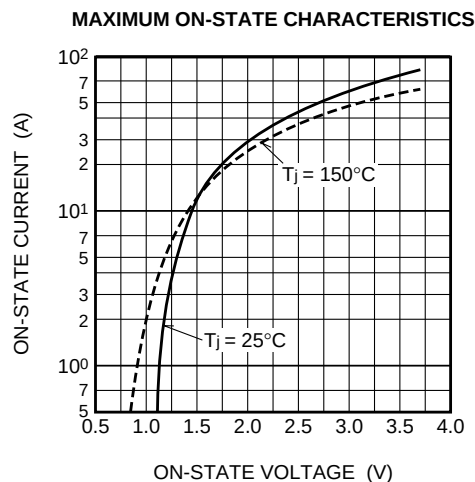
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*3. Case temperature is measured on the T2 terminal.

*4. The contact thermal resistance $R_{th(c-j)}$ in case of greasing is $1.0^{\circ}\text{C}/\text{W}$.

*5. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.

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1. Junction temperature $T_J=125^{\circ}\text{C}/150^{\circ}\text{C}$ 2. Rate of decay of on-state commutating current $(di/dt)_c=-4.0\text{A}/\text{ms}$ 3. Peak off-state voltage $V_D=400\text{V}$	

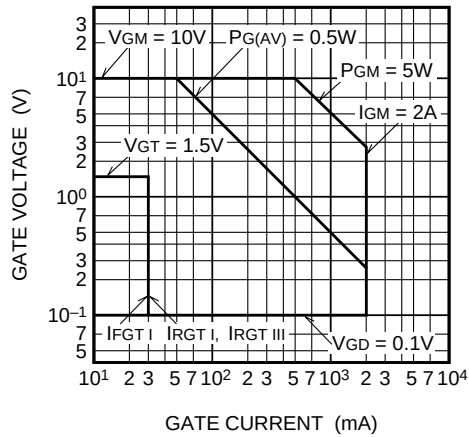
PERFORMANCE CURVES

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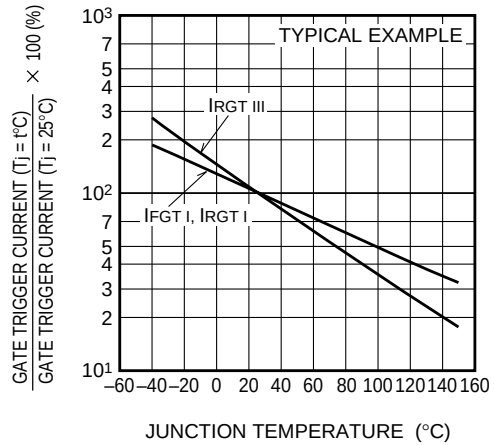
The product guaranteed maximum junction temperature 150°C (See warning.)

MEDIUM POWER USE
NON-INSULATED TYPE, PLANAR PASSIVATION TYPE

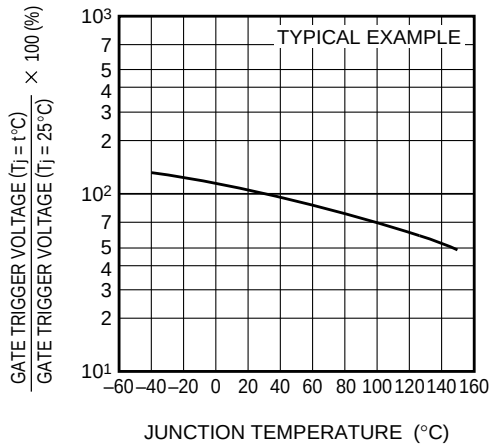
**GATE CHARACTERISTICS
(I, II AND III)**



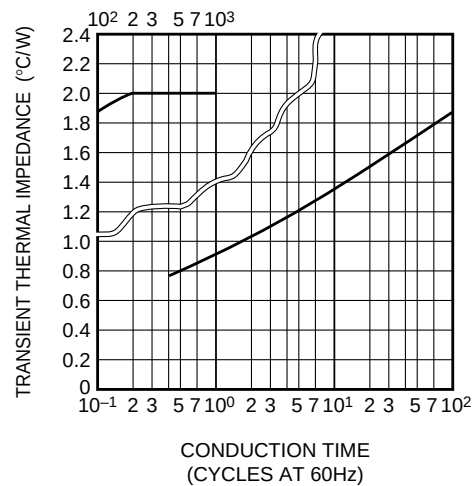
**GATE TRIGGER CURRENT VS.
JUNCTION TEMPERATURE**



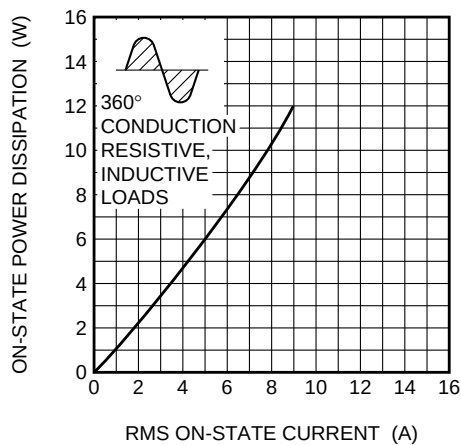
**GATE TRIGGER VOLTAGE VS.
JUNCTION TEMPERATURE**



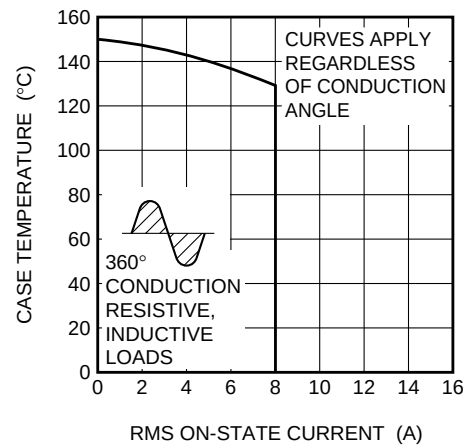
**MAXIMUM TRANSIENT THERMAL
IMPEDANCE CHARACTERISTICS
(JUNCTION TO CASE)**



**MAXIMUM ON-STATE POWER
DISSIPATION**



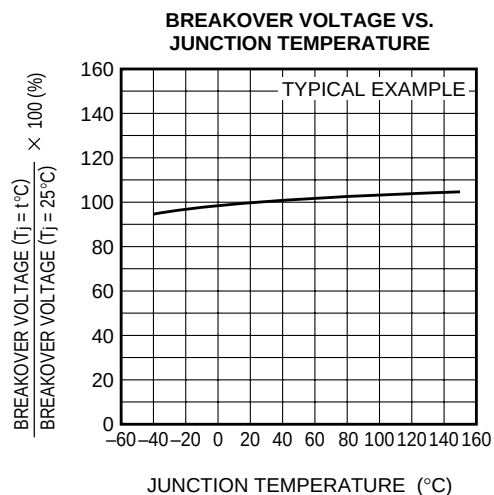
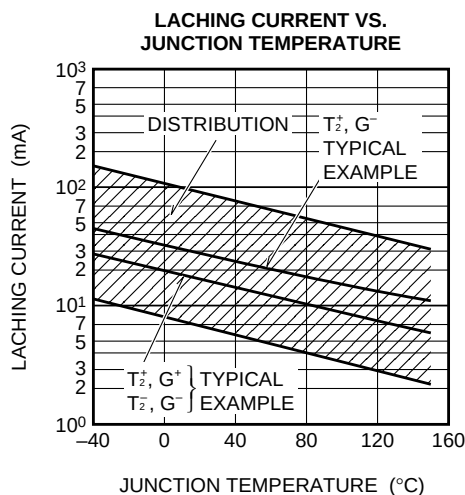
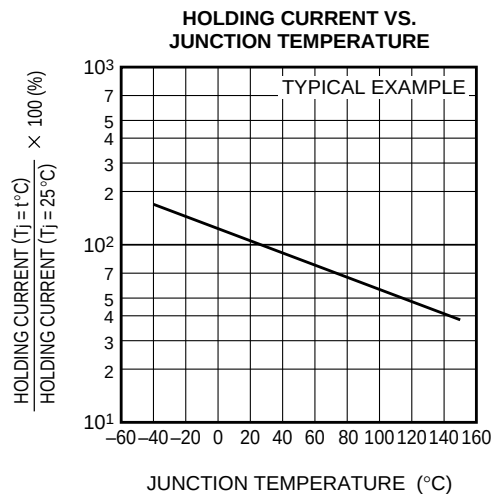
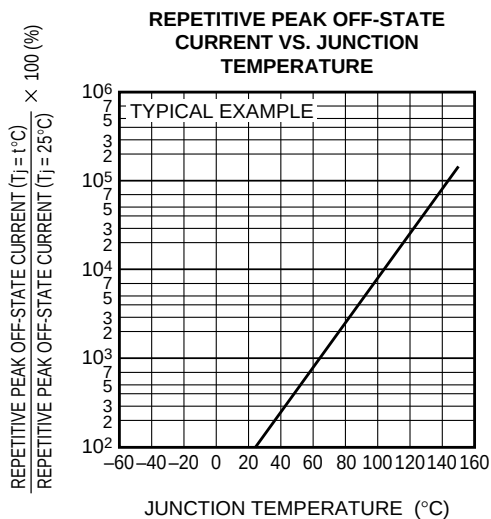
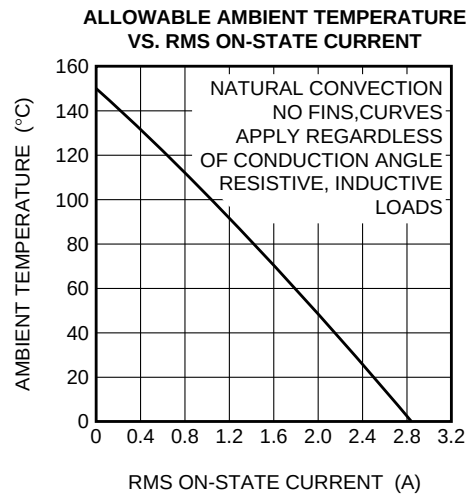
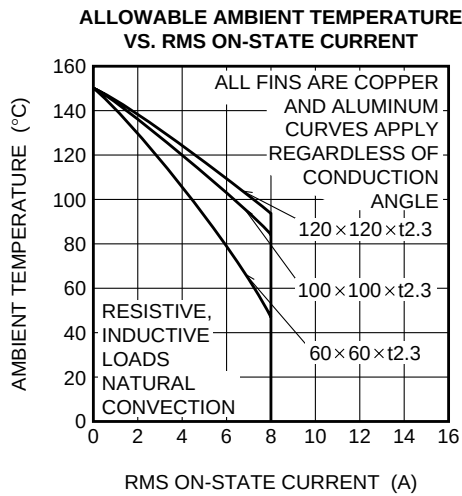
**ALLOWABLE CASE TEMPERATURE
VS. RMS ON-STATE CURRENT**



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The product guaranteed maximum junction temperature 150°C (See warning.)

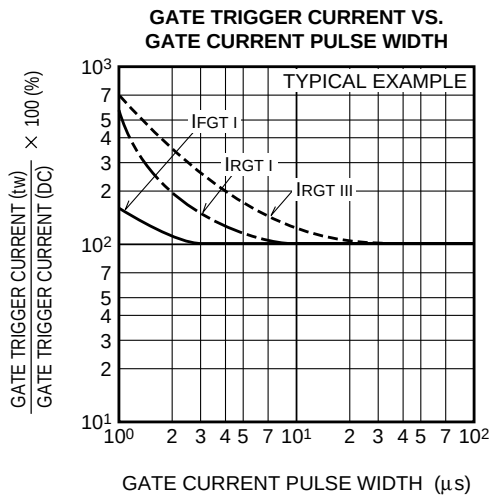
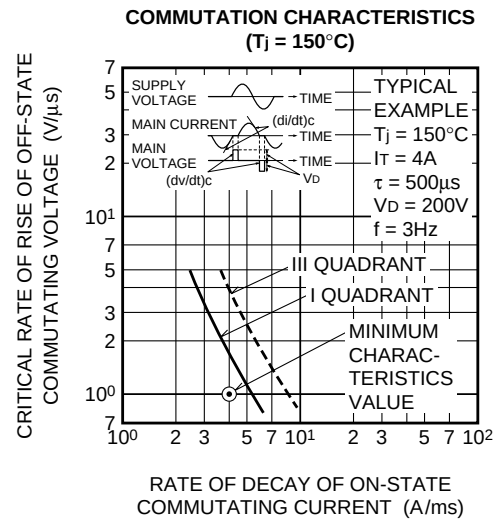
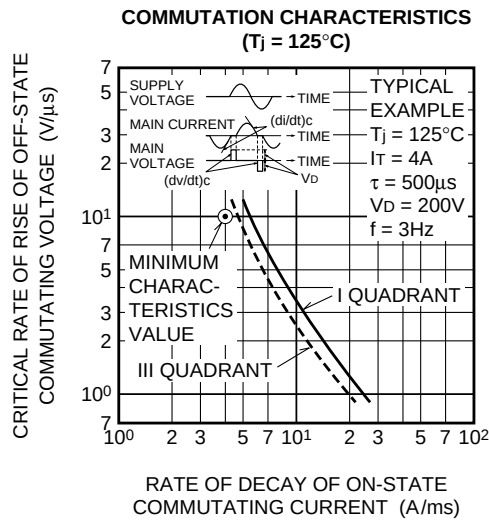
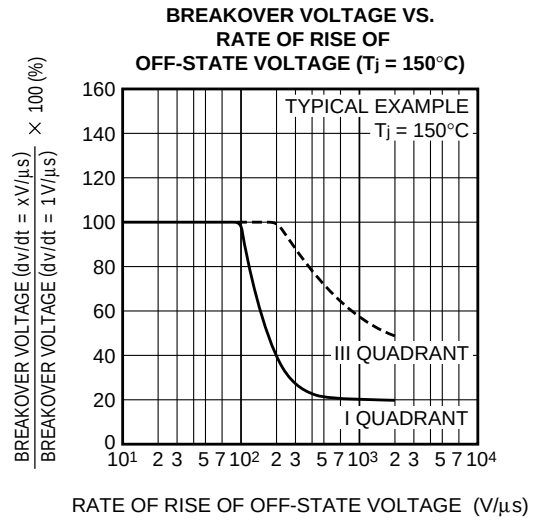
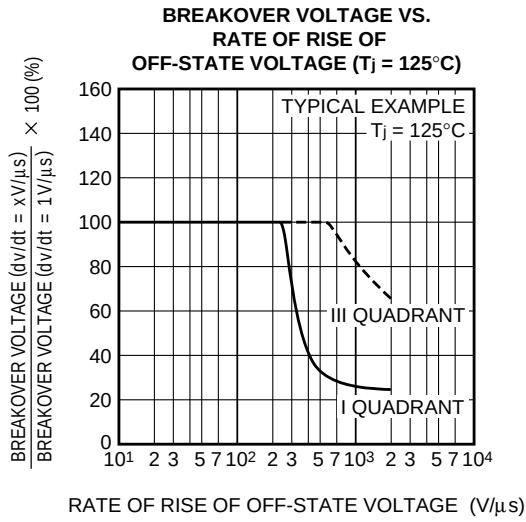
MEDIUM POWER USE
NON-INSULATED TYPE, PLANAR PASSIVATION TYPE



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NON-INSULATED TYPE, PLANAR PASSIVATION TYPE

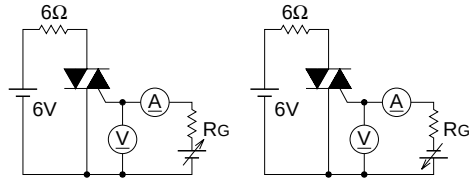


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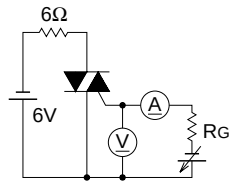
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MEDIUM POWER USE
NON-INSULATED TYPE, PLANAR PASSIVATION TYPE

GATE TRIGGER CHARACTERISTICS TEST CIRCUITS

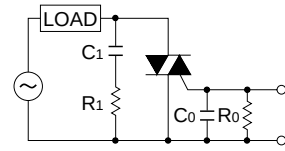


TEST PROCEDURE I TEST PROCEDURE II



TEST PROCEDURE III

RECOMMENDED CIRCUIT VALUES AROUND THE TRIAC



$C_1 = 0.1 \sim 0.47 \mu\text{F}$ $C_0 = 0.1 \mu\text{F}$
 $R_1 = 47 \sim 100 \Omega$ $R_0 = 100 \Omega$